Boron in Silicon implant

Depth vs. Y-Axis

+ 1750 A

Layer 1

-1750 A

0 A — Target Depth — 3500 A
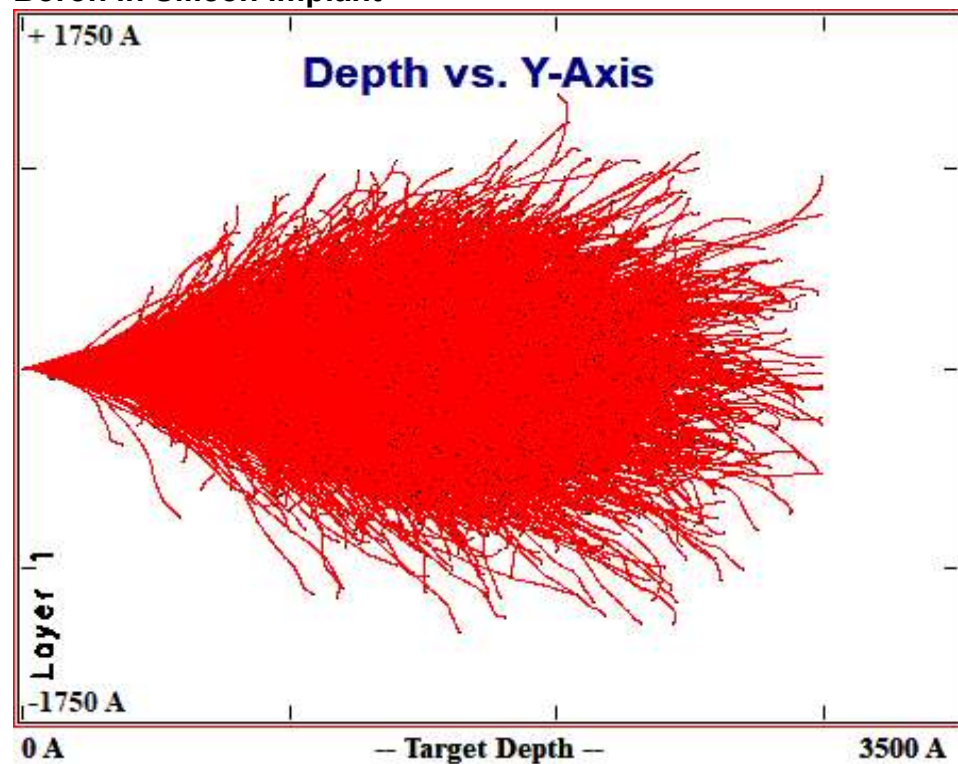
9999 Ions Calculated

Ion Type = In
Ion Energy = 325 keV
Ion Angle = 0

Calculation Parameters:

Backscattered Ions	0
Transmitted Ions	7
Vacancies/Ion	4982.9

ION STATS

	Range	Straggle
Longitudinal	1522 A	448 A
Lateral Proj.	248 A	317 A
Radial	391 A	222 A

Type of Damage Calculation
Quick: Kinchin-Pease

Stopping Power Version
SRIM-2008

% ENERGY	LOSS Ions	Recoils
Ionization	11.69	30.68
Vacancies	0.10	2.96
Phonons	0.21	54.35

SPUTTERING YIELD

	Atoms/Ion	eV/Atom
TOTAL		
Si	0.000000	0.00

Target layers:

	Layer Name	Width (A)	Density	Si (28.086)	Solid/Gas	Stop Corr.
1	Layer 1	3000	2.321	1.00000	Solid	1
	Lattice Binding Energy			2		
	Surface Binding Energy			4.7		
	Displacement Energy			15		